# BLP9G0722-20; BLP9G0722-20G Power LDMOS transistor

**AMPLEON** 

Rev. 3 — 26 February 2018

Product data sheet

# **Product profile**

### 1.1 General description

20 W plastic LDMOS power transistor for base station applications at frequencies from 100 MHz to 2700 MHz.

**Application performance (multiple frequencies)** 

Typical RF performance at  $T_{case}$  = 25 °C;  $I_{Da}$  = 180 mA; in a class-AB demo board, tested on gull wing lead device.

Test signal	f	I <sub>Dq</sub>	V <sub>DS</sub>	P <sub>L(AV)</sub>	Gp	ηр	ACPR <sub>5M</sub>
	(MHz)	(mA)	(V)	(dBm)	(dB)	(%)	(dBc)
1-carrier W-CDMA	400 to 430	180	28	35	25.5	24	-45 <sup>[1]</sup>
	728 to 768	180	28	35	23	22	-45 <u>[1]</u>
	1805 to 1880	180	28	35	19	21	-45 <u>[1]</u>
	2110 to 2170	180	28	35	18	21	-45 <u>[1]</u>
	2300 to 2400	180	28	35	17.3	21	-45 <u>[1]</u>
	2570 to 2620	180	28	35	16	20	-45 <u>[1]</u>

<sup>[1]</sup> Test signal: 3GPP test model 1; 64 DCHP; PAR = 7.2 dB at 0.01 % probability on CCDF.

#### 1.2 Features and benefits

- High efficiency
- Excellent ruggedness
- Designed for broadband operation
- Excellent thermal stability
- High power gain
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

### 1.3 Applications

■ FDD/TDD LTE

W-CDMA

GSM EDGE

MC-GSM

CDMA

■ WiMAX

# 2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
BLP9G07	722-20 (SOT1482-1)			
1	drain		2	
2	gate			1 L
3	source	[1]	3 0	2 — 3 3 sym112
BLP9G07	722-20G (SOT1483-1)			
1	drain		2	
2	gate			1 L
3	source	[1]	3 0	2 — 3 3 sym112

<sup>[1]</sup> Connected to flange.

# 3. Ordering information

Table 3. Ordering information

Type number	Package	ıckage				
	Name	Description	Version			
BLP9G0722-20	-	plastic; heatsink small outline package; 2 leads (flat)	SOT1482-1			
BLP9G0722-20G	-	plastic; heatsink small outline package; 2 leads	SOT1483-1			

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	65	V
$V_{GS}$	gate-source voltage		-5	+13	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	225	°C

# 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-c)</sub>	thermal resistance from junction to case	$T_{case}$ = 80 °C; $P_L$ = 3 W	1.1	K/W

### 6. Characteristics

Table 6. DC characteristics

 $T_i = 25 \, ^{\circ}\text{C}$ ; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.3 \text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_D = 30 \text{ mA}$	1.5	2.0	-	V
$V_{GSq}$	gate-source quiescent voltage	V <sub>DS</sub> = 28 V; I <sub>D</sub> = 180 mA	1.6	2.1	2.6	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 28 V	-	-	1.4	μА
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 V$	-	6	-	Α
$I_{GSS}$	gate leakage current	$V_{GS} = 11 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	140	nA
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; $I_{D}$ = 30 mA	-	300	-	mS
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 V;$ $I_D = 1.05 A$	-	500	-	mΩ

#### Table 7. RF characteristics

A derivative functional RF test is performed in production. The performance as mentioned below is verified by design and characterization in a class AB production board.

Test signal: pulsed CW;  $\delta$  = 10%;  $t_p$  = 100  $\mu$ s;  $V_{DS}$  = 28 V;  $I_{Dq}$  = 180 mA;  $T_{case}$  = 25 °C; f = 1842.5 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	$P_{L(AV)} = 35 \text{ dBm}$	17	19	-	dB
$\eta_{D}$	drain efficiency	$P_{L(AV)} = 35 \text{ dBm}$	18	22	-	%
RLin	input return loss	$P_{L(AV)} = 35 \text{ dBm}$	-	-10	-6	dB
P <sub>L(1dB)</sub>	output power at 1 dB gain compression		42.5	43.9	-	dBm
P <sub>L(3dB)</sub>	output power at 3 dB gain compression		43	44.3	-	dBm

### 7. Test information

## 7.1 Ruggedness in Doherty operation

The BLP9G0722-20 and BLP9G0722-20G are capable of withstanding a load mismatch corresponding to a VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS} = 28 \text{ V}$ ;  $P_L = 20 \text{ W}$  (CW); f = 728 MHz and 1805 MHz on development board.

### 7.2 Impedance information

Table 8. Typical impedance of BLP9G0722-20G

Measured load-pull data;  $I_{Dq} = 180 \text{ mA}$ ;  $V_{DS} = 28 \text{ V}$ .

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <sub>D</sub> [2]	G <sub>p</sub> [2]
(MHz)	<b>(</b> Ω <b>)</b>	<b>(Ω)</b>	(W)	(%)	(dB)
Maximum pov	wer load				
740	0.5 + j0.1	10.6 – j1.0	37	55.1	22.8
880	0.6 – j1.4	3.8 + j2.0	49	70.9	22.8
1810	1.6 – j5.5	3.4 – j1.0	43	62.2	19.0

BLP9G0722-20\_9G0722-20G

Table 8. Typical impedance of BLP9G0722-20G ...continued

Measured load-pull data;  $I_{Dq} = 180 \text{ mA}$ ;  $V_{DS} = 28 \text{ V}$ .

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <sub>D</sub> [2]	G <sub>p</sub> [2]
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)
1840	1.3 – j5.8	3.0 – j1.2	43	62.7	19.1
1880	1.3 – j6.2	2.6 – j1.5	42	61.2	18.7
2110	5.3 – j9.6	2.6 – j2.5	41	58.2	17.7
2170	6.2 – j8.1	2.6 – j2.5	41	60.4	18.2
Maximum dra	ain efficiency load				
740	0.5 + j0.1	6.0 + j10.0	20	74.1	24.8
880	0.6 – j1.4	3.7 + j5.9	26	82.7	24.7
1810	1.6 – j5.5	1.9 + j0.2	31	70.9	20.9
1840	1.3 – j5.8	1.7 + j0.0	29	69.8	21.3
1880	1.3 – j6.2	1.6 – j0.2	28	69.8	21.3
2110	5.3 – j9.6	1.7 – j1.5	32	65.6	19.5
2170	6.2 – j8.1	1.6 – j1.7	30	65.9	20.2

<sup>[1]</sup>  $Z_S$  and  $Z_L$  defined in Figure 1.

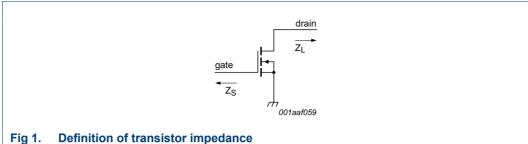
Table 9. Typical impedance of BLP9G0722-20 Measured load-pull data;  $I_{Dq}$  = 180 mA;  $V_{DS}$  = 28 V.

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <sub>D</sub> [2]	G <sub>p</sub> [2]
(MHz)	(Ω)	<b>(</b> Ω <b>)</b>	(W)	(%)	(dB)
Maximum po	wer load				
740	0.6 + j0.6	10.6 – j1.0	39	56.8	22.7
880	0.6 – j0.7	4.0 + j1.6	51	70.9	22.1
1810	1.8 – j5.4	3.0 – j1.2	44	60.9	19.1
1840	1.6 – j5.8	3.0 – j1.2	44	62.6	19.6
1880	1.8 – j6.1	2.9 – j1.6	44	60.9	19.1
2110	7.3 – j8.2	2.6 – j2.5	41	57.7	17.8
2170	8.7 – j6.8	2.6 – j2.5	43	62.1	18.7
Maximum dra	ain efficiency load				
740	0.6 + j0.6	6.0 + j10.0	22	77.0	24.6
880	0.6 – j0.7	3.7 + j5.9	26	85.3	24.4
1810	1.8 – j5.4	1.9 + j0.0	33	69.4	20.9
1840	1.6 – j5.8	1.9 + j0.0	31	69.4	21.7
1880	1.8 – j6.1	1.8 – j0.2	32	70.7	21.6
2110	7.3 – j8.2	1.5 – j1.4	30	65.3	19.9
2170	8.7 – j6.8	1.4 – j1.6	29	69.3	21.3

<sup>[1]</sup>  $Z_S$  and  $Z_L$  defined in <u>Figure 1</u>.

<sup>[2]</sup> at 3 dB gain compression.

<sup>[2]</sup> at 3 dB gain compression.



### 7.3 Test circuit

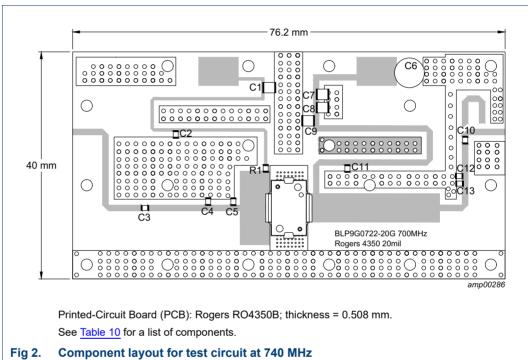


Table 10. List of components See Figure 2 for component layout.

Component	Description	Value	Remarks
C1, C7, C8, C9	multilayer ceramic chip capacitor	10 μF, 50 V	Murata
C2, C3, C10, C11	multilayer ceramic chip capacitor	36 pF	ATC 600F
C4, C5	multilayer ceramic chip capacitor	15 pF	ATC 600F
C6	electrolytic capacitor	2200 μF, 50 V	
C12	multilayer ceramic chip capacitor	5.6 pF	ATC 600F
C13	multilayer ceramic chip capacitor	0.2 pF	ATC 600F
R1	resistor	5.1 Ω	SMD 0805

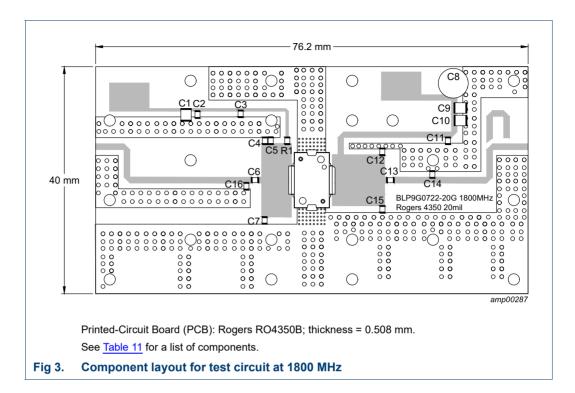


Table 11. List of components

See Figure 3 for component layout.

Component	Description	Value	Remarks
C1, C9, C10	multilayer ceramic chip capacitor	10 μF, 50 V	Murata
C2, C3, C11, C13	multilayer ceramic chip capacitor	12 pF	ATC 600F
C4, C5	multilayer ceramic chip capacitor	0.8 pF	ATC 600F
C6	multilayer ceramic chip capacitor	6.2 pF	ATC 600F
C7	multilayer ceramic chip capacitor	2 pF	ATC 600F
C8	electrolytic capacitor	2200 μF, 50 V	
C12, C15	multilayer ceramic chip capacitor	0.3 pF	ATC 600F
C14	multilayer ceramic chip capacitor	2.2 pF	ATC 600F
C16	multilayer ceramic chip capacitor	0.3 pF	ATC 600F
R1	resistor	5.1 Ω	SMD 0805

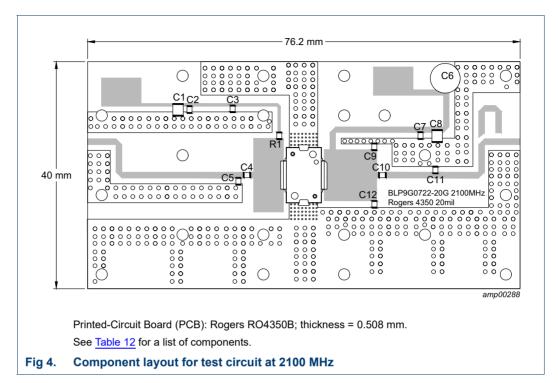


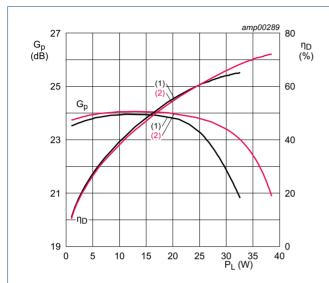
Table 12. List of components

See Figure 4 for component layout.

Component	Description	Value	Remarks
C1, C8	multilayer ceramic chip capacitor	10 μF, 50 V	Murata
C2, C7, C10	multilayer ceramic chip capacitor	12 pF	ATC 600F
C3	multilayer ceramic chip capacitor	62 pF	ATC 600F
C4	multilayer ceramic chip capacitor	5.6 pF	ATC 600F
C5	multilayer ceramic chip capacitor	0.5 pF	ATC 600F
C6	electrolytic capacitor	2200 μF, 50 V	
C9	multilayer ceramic chip capacitor	2.2 pF	ATC 600F
C11	multilayer ceramic chip capacitor	1.2 pF	ATC 600F
C12	multilayer ceramic chip capacitor	1.8 pF	ATC 600F
R1	resistor	5.1 Ω	SMD 0805

### 7.4 Graphical data

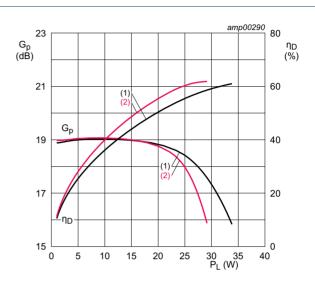
#### 7.4.1 CW



 $V_{DS} = 28 \text{ V}; I_{Dq} = 180 \text{ mA}.$ 

- (1) f = 728 MHz
- (2) f = 768 MHz

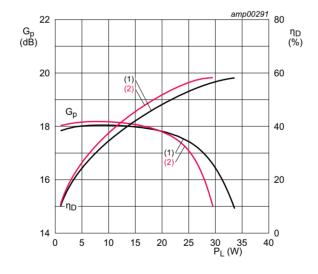
Fig 5. Power gain and drain efficiency as function of output power; typical values



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 180 mA.

- (1) f = 1805 MHz
- (2) f = 1880 MHz

Fig 6. Power gain and drain efficiency as function of output power; typical values

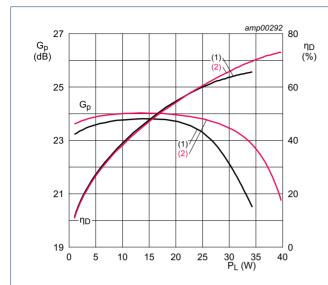


 $V_{DS} = 28 \text{ V}; I_{Dq} = 180 \text{ mA}.$ 

- (1) f = 2110 MHz
- (2) f = 2170 MHz

Fig 7. Power gain and drain efficiency as function of output power; typical values

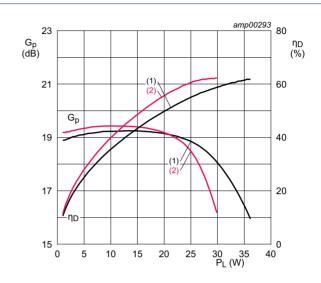
#### 7.4.2 Pulsed CW



 $V_{DS} = 28 \text{ V}; I_{Dq} = 180 \text{ mA}.$ 

- (1) f = 728 MHz
- (2) f = 768 MHz

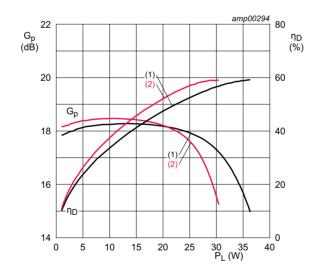
Fig 8. Power gain and drain efficiency as function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 180 \text{ mA}.$ 

- (1) f = 1805 MHz
- (2) f = 1880 MHz

Fig 9. Power gain and drain efficiency as function of output power; typical values

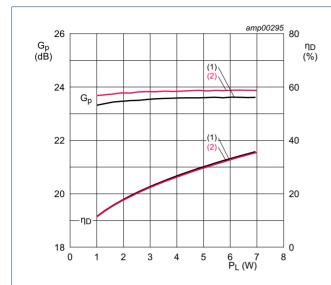


 $V_{DS} = 28 \text{ V}; I_{Dq} = 180 \text{ mA}.$ 

- (1) f = 2110 MHz
- (2) f = 2170 MHz

Fig 10. Power gain and drain efficiency as function of output power; typical values

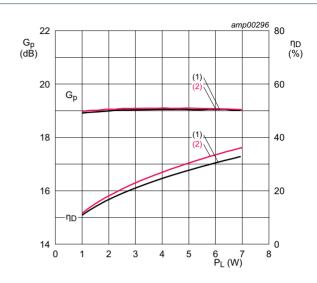
#### 7.4.3 1-Carrier W-CDMA



 $V_{DS} = 28 \text{ V}; I_{Dq} = 180 \text{ mA}.$ 

- (1) f = 728 MHz
- (2) f = 768 MHz

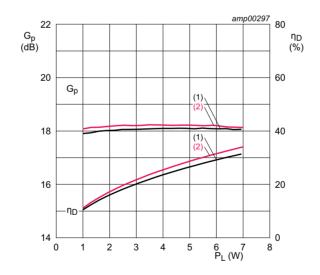
Fig 11. Power gain and drain efficiency as function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 180 \text{ mA}.$ 

- (1) f = 1805 MHz
- (2) f = 1880 MHz

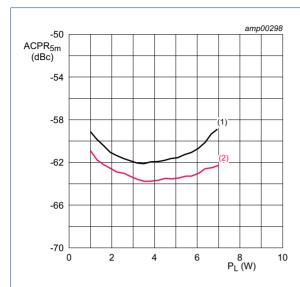
Fig 12. Power gain and drain efficiency as function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 180 \text{ mA}.$ 

- (1) f = 2110 MHz
- (2) f = 2170 MHz

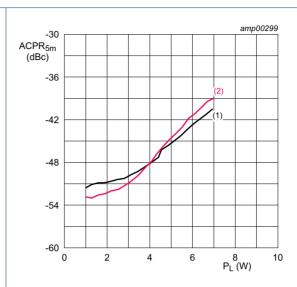
Fig 13. Power gain and drain efficiency as function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 180 \text{ mA}.$ 

- (1) f = 728 MHz
- (2) f = 768 MHz

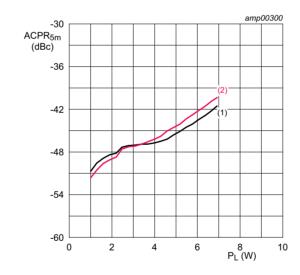
Fig 14. Adjacent channel power ratio (5 MHz) as a function of output power; typical values



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 180 mA.

- (1) f = 1805 MHz
- (2) f = 1880 MHz

Fig 15. Adjacent channel power ratio (5 MHz) as a function of output power; typical values



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 180 mA.

- (1) f = 2110 MHz
- (2) f = 2170 MHz

Fig 16. Adjacent channel power ratio (5 MHz) as a function of output power; typical values

# 8. Package outline

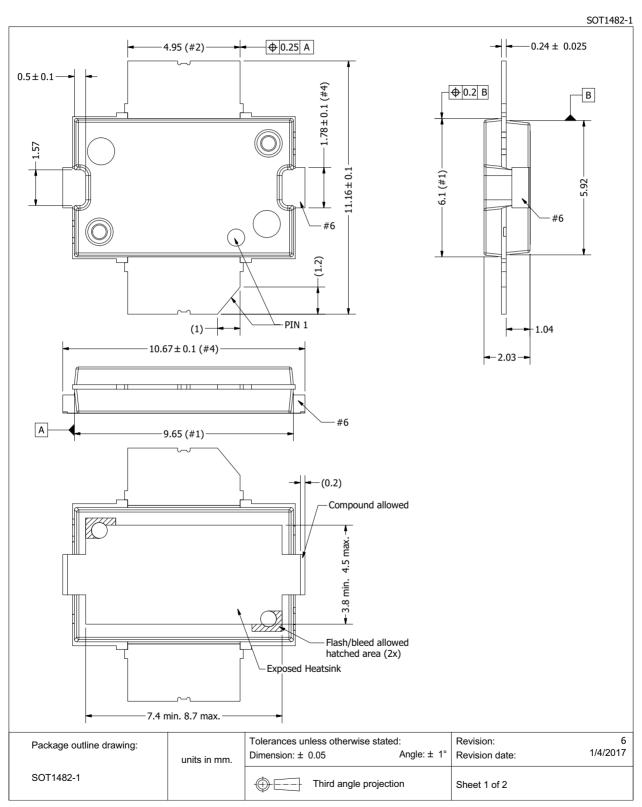
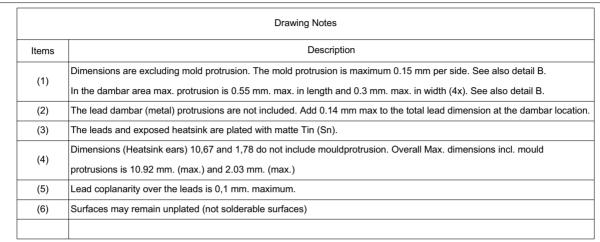


Fig 17. Package outline SOT1482-1 (sheet 1 of 2)

BLP9G0722-20\_9G0722-20G

#### SOT1482-1



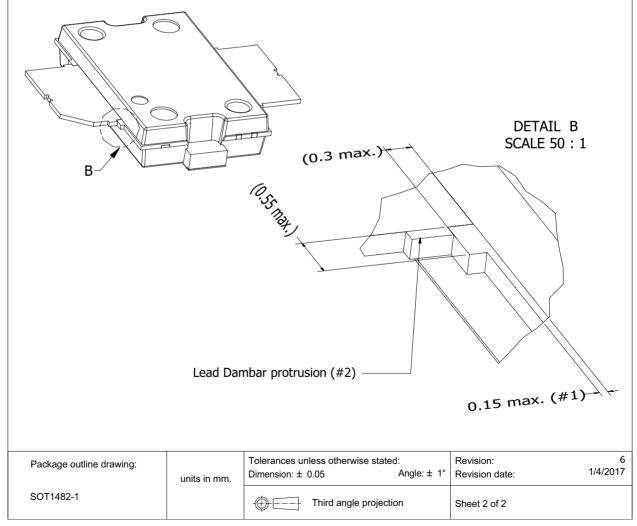


Fig 18. Package outline SOT1482-1 (sheet 2 of 2)

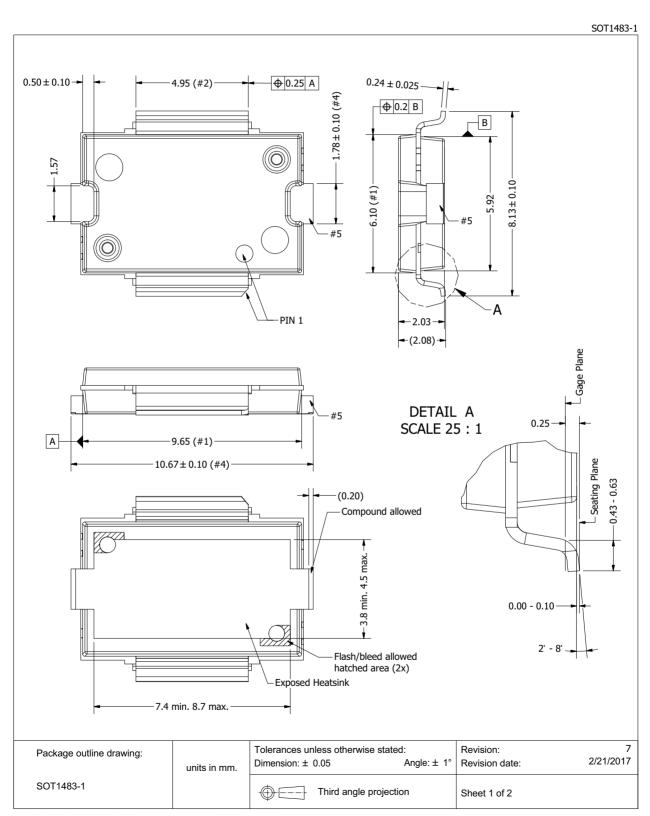
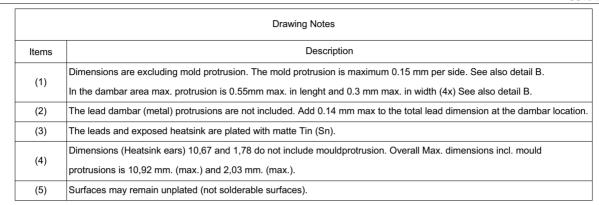


Fig 19. Package outline SOT1483-1 (sheet 1 of 2)

BLP9G0722-20\_9G0722-20G

#### SOT1483-1



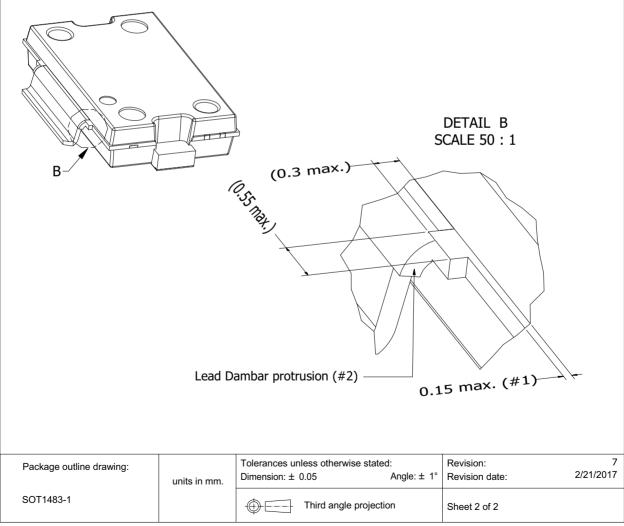


Fig 20. Package outline SOT1483-1 (sheet 2 of 2)

# 9. Handling information

#### **CAUTION**



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 13. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

- [1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V, but fails after exposure to an ESD pulse of 750 V.
- [2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V, but fails after exposure to an ESD pulse of 4000 V.

# 10. Abbreviations

Table 14. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CDMA	Code Division Multiple Access
CW	Continuous Wave
DCPH	Dedicated Physical CHannel
EDGE	Enhanced Data rates for GSM Evolution
ESD	ElectroStatic Discharge
FDD	Frequency Division Duplex
GSM	Global System for Mobile Communication
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
LTE	Long Term Evolution
MC-GSM	Multi Carrier GSM
MTF	Median Time to Failure
PAR	Peak-to-Average Ratio
SMD	Surface Mounted Device
TDD	Time Division Duplex
W-CDMA	Wideband Code Division Multiple Access
WiMAX	Worldwide Interoperability for Microwave Access

# 11. Revision history

### Table 15. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLP9G0722-20_9G0722-20G v.3	20180226	Product data sheet	-	BLP9G0722-20_9G0722-20G v.2
Modifications:	Section 1.1 on page 1: changed "400 MHz" to "100 MHz"			
BLP9G0722-20_9G0722-20G v.2	20170801	Product data sheet	-	BLP9G0722-20_9G0722-20G v.1
BLP9G0722-20_9G0722-20G v.1	20170606	Product data sheet	-	-

# 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.ampleon.com.

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### 13. Contact information

For more information, please visit: http://www.ampleon.com

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# **AMPLEON**

**Power LDMOS transistor** 

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